

2MBI1400VXB-170E-50

IGBT Modules

IGBT MODULE (V series) 1700V / 1400A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Conditions		Units	
Collector-Emitter voltage	Vces			1700	V	
Gate-Emitter voltage	V _{GES}			±20	V	
	Ic	Continuous	Tc=25°C	1800		
<u>‡</u>		Continuous	Tc=100°C	1400		
S Collector current	Ic pulse	1ms		2800	Α	
드	-Ic			1400		
	-I _{c pulse}	1ms		2800		
Collector power dissipation	Pc	1 device		8820	W	
Junction temperature	T _j			175		
Operating junction temperature (under switching conditions	T _{jop}			150	°C	
Case temperature	Tc			150		
Storage temperature	T _{stg}					
Isolation voltage between terminal and copper base (*1)	V _{iso}	AC : 1min.	AC : 1min		VAC	
between thermistor and others (*2)		AC . IIIIII.		4000	VAC	
Mounting		M5	M5			
Screw torque (*3) Main Terminals	_	M8	M8		N m	
Sense Terminals		M4		2.1		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value: Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value: Main Terminals 8.0 ~ 10.0 Nm (M8)

Recommendable Value: Sense Terminals 1.8 ~ 2.1 Nm (M4)

Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Cumbala	Conditions		Characteristics			l lmita
		Symbols			min.	typ.	max.	Units
Zero	o gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1700V		-	-	12.0	mA
Gat	e-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	2400	nA
Gat	e-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 1400mA		6.0	6.5	7.0	V
		V _{CE (sat)}		T _j =25°C	-	2.35	2.80	V
		(terminal)		T _j =125°C	-	2.85	-	
0.11	la stan Fusittan a stumstian	(*4)	V _{GE} = 15V I _C = 1400A	T _j =150°C	-	2.95	-	
Coll	Collector-Emitter saturation voltage			T _i =25°C	-	2.15	2.60	
		V _{CE} (sat)		T _i =125°C	-	2.65	-	
	(chip)		T _i =150°C	-	2.75	-	1	
Inte	rnal gate resistance	Rg(int)	-	,	-	2.25	-	Ω
	ut capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	113	-	nF
5		ton	-		-	1350	-	
Turn-on time	n-on time	tr			-	300	-	
	tr (i)	Vcc=900V, I₀=1400A, V⋳∈±±15V, R₀=+0.47/-0.68Ω, Ls=40nH		-	150	-	nsec	
	toff			-	1600	-		
Turi	Turn-off time	tf	1		_	150	-	1
	Forward on voltage	VF		T _i =25°C	-	2.00	2.45	
		(terminal)		T _i =125°C	-	2.25	-	V
1_		(*4)	$V_{GF} = 0V$	T _i =150°C	-	2.20	-	
For		,	I _F = 1400A	T _i =25°C	-	1.80	2.25	
		V _F		T _i =125°C	-	2.05	-	
	(chip)		T=150°C	-	2.00	-		
Rev	verse recovery time	trr	I _F = 1400A		-	250	-	nsec
2 _			T=25°C		-	5000	-	
Resistance	R	T=100°C		465	495	520	Ω	
Res B va	alue	В	T=25/50°C		3305	3375	3450	K

Note *4: Please refer to Page 6, there is definition of on-state voltage at terminal.

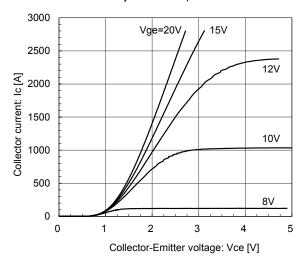
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units	
Items			min.	typ.	max.	Units	
Thermal resistance (1device)	Rth(j-c)	Inverter IGBT	-	-	0.017	°C/W	
		Inverter FWD	-	-	0.032		
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0042	-		

■ Characteristics (Representative)

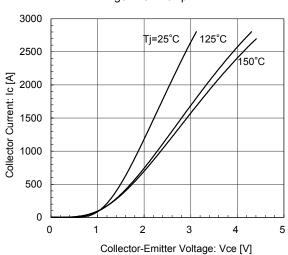
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



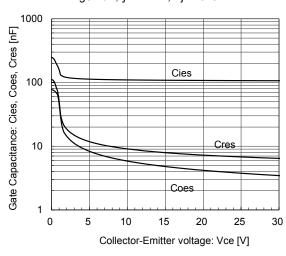
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Vge= 15V / chip



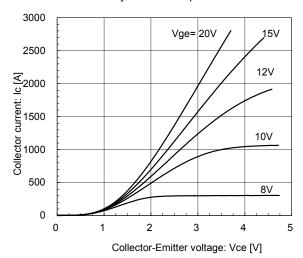
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) Vge= 0V, f= 1MHz, Tj= 25°C



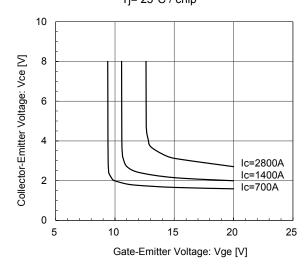
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Ti= 150°C / chip



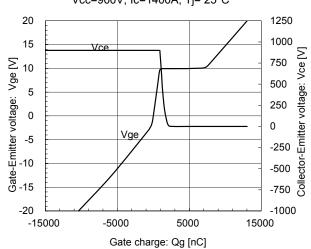
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip

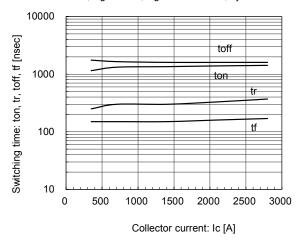


[INVERTER]

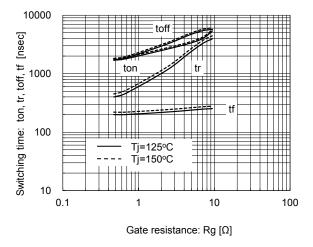
Dynamic Gate Charge (typ.) Vcc=900V, Ic=1400A, Tj= 25°C



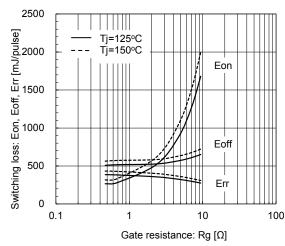
[INVERTER] Switching time vs. Collector current (typ.) Vcc=900V, Vge= \pm 15V, Rg= \pm 0.47/-0.68 Ω , Tj=25°C



[INVERTER]
Switching time vs. Gate resistance (typ.)
Vcc=900V, Ic=1400A, Vge=±15V, Tj=125°C, 150°C

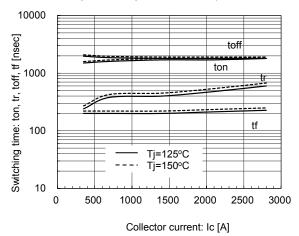


[INVERTER]
Switching loss vs. Gate resistance (typ.)
Vcc=900V, Ic=1400A, Vge=±15V, Tj=125°C, 150°C

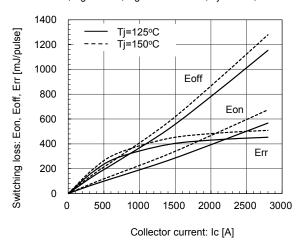


[INVERTER]

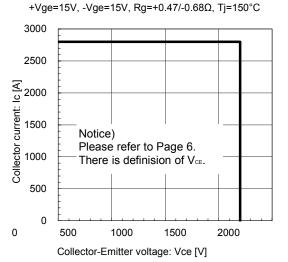
Switching time vs. Collector current (typ.) Vcc=900V, Vge= \pm 15V, Rg= \pm 0.47/-0.68 Ω , Tj=125°C, 150°C



[INVERTER] Switching loss vs. Collector current (typ.) Vcc=900V, Vge= \pm 15V, Rg= \pm 0.47/-0.68 Ω , Tj=125°C, 150°C



[INVERTER]
Reverse bias safe operating area (max.)



[INVERTER] Forward Current vs. Forward Voltage (typ.) chip 3000 2500 Tj=25° 2000 1500 25° C 1000 500 0

Forward current: If [A] 0 1 2 2 3 3 Forward on voltage: Vf [V]

10000 Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] 1000 Irr trr 100 10 0 500 1000 1500 2000 2500 3000 Forward current: If [A]

[INVERTER] Reverse Recovery Characteristics (typ.)

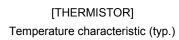
Vcc=900V, Vge=±15V, Rg=+0.47/-0.68Ω, Tj=25°C

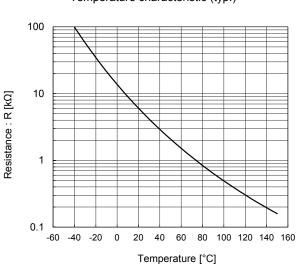
Vcc=900V, Vge=±15V, Rg=+0.47/-0.68Ω, Tj=125°C, 150°C 10000 Tj=125°C Tj=150°C Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] lrr 1000 100 10 0 500 2500 3000 1000 1500 2000 Forward current: If [A]

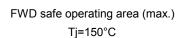
[INVERTER] Reverse Recovery Characteristics (typ.)

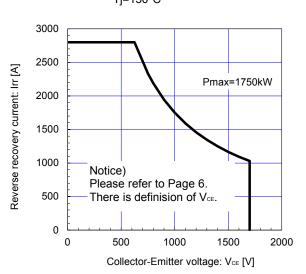
0.1 **FWD** Thermal resistanse: Rth(j-c) [°C/W] 0.01 0.001 0.0023 0.0301 0.0001 0.001 0.01 0.1 Pulse Width: Pw [sec]

Transient Thermal Resistance (max.)



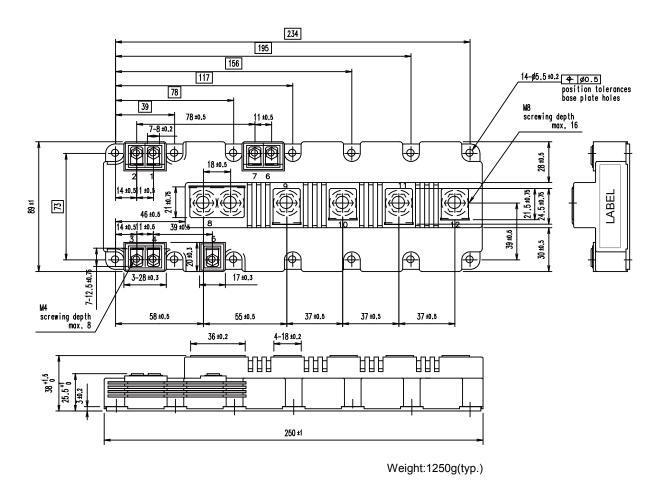




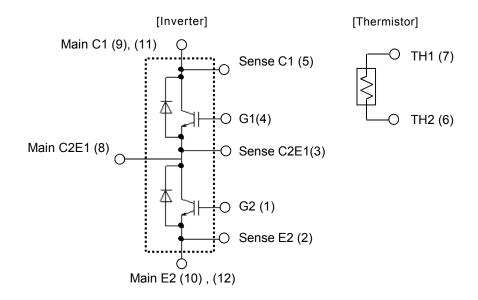


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■ Outline Drawings, mm

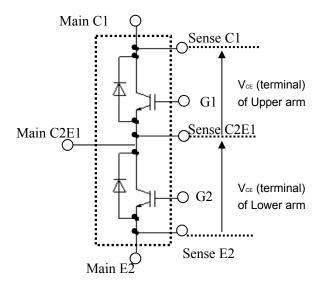


■ Equivalent Circuit Schematic



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■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined V_{CE} value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Switching characteristics of V_{CE} also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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- Measurement equipment

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